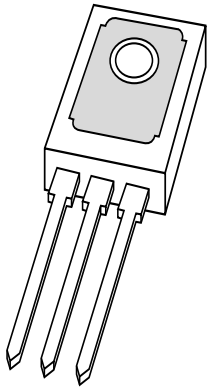


# DATA SHEET



## **BDX45; BDX47** PNP Darlington transistors

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 Jul 02

# PNP Darlington transistors

# BDX45; BDX47

### FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

### APPLICATIONS

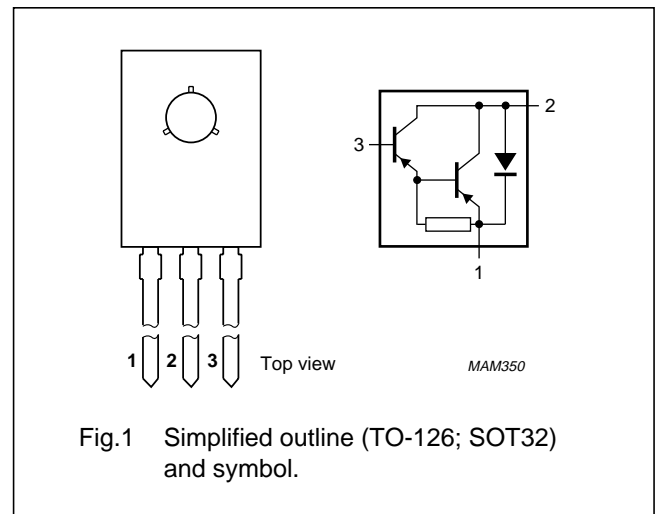
- Industrial switching applications such as:
  - print hammers
  - solenoids
  - relay and lamp drivers.

### DESCRIPTION

PNP Darlington transistor in a TO-126; SOT32 plastic package. NPN complements: BDX42 and BDX44.

### PINNING

PIN	DESCRIPTION
1	emitter
2	collector, connected to metal part of mounting surface
3	base



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage BDX45 BDX47	open emitter	–	–	–60	V
			–	–	–90	V
V <sub>CES</sub>	collector-emitter voltage BDX45 BDX47	V <sub>BE</sub> = 0	–	–	–45	V
			–	–	–80	V
I <sub>C</sub>	collector current (DC)		–	–	–1	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	–	1.25	W
		T <sub>mb</sub> ≤ 100 °C	–	–	5	W
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = –150 mA; V <sub>CE</sub> = –10 V	1000	–	–	
		I <sub>C</sub> = –500 mA; V <sub>CE</sub> = –10 V	2000	–	–	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = –500 mA; V <sub>CE</sub> = –5 V; f = 100 MHz	–	200	–	MHz

## PNP Darlington transistors

## BDX45; BDX47

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BDX45		–	–60	V
	BDX47		–	–90	V
V <sub>CES</sub>	collector-emitter voltage	V <sub>BE</sub> = 0			
	BDX45		–	–45	V
	BDX47		–	–80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–1	A
I <sub>CM</sub>	peak collector current		–	–2	A
I <sub>B</sub>	base current (DC)		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	1.25	W
		T <sub>mb</sub> ≤ 100 °C	–	5	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air	100	K/W
R <sub>th j-mb</sub>	thermal resistance from junction to mounting base		10	K/W

## PNP Darlington transistors

## BDX45; BDX47

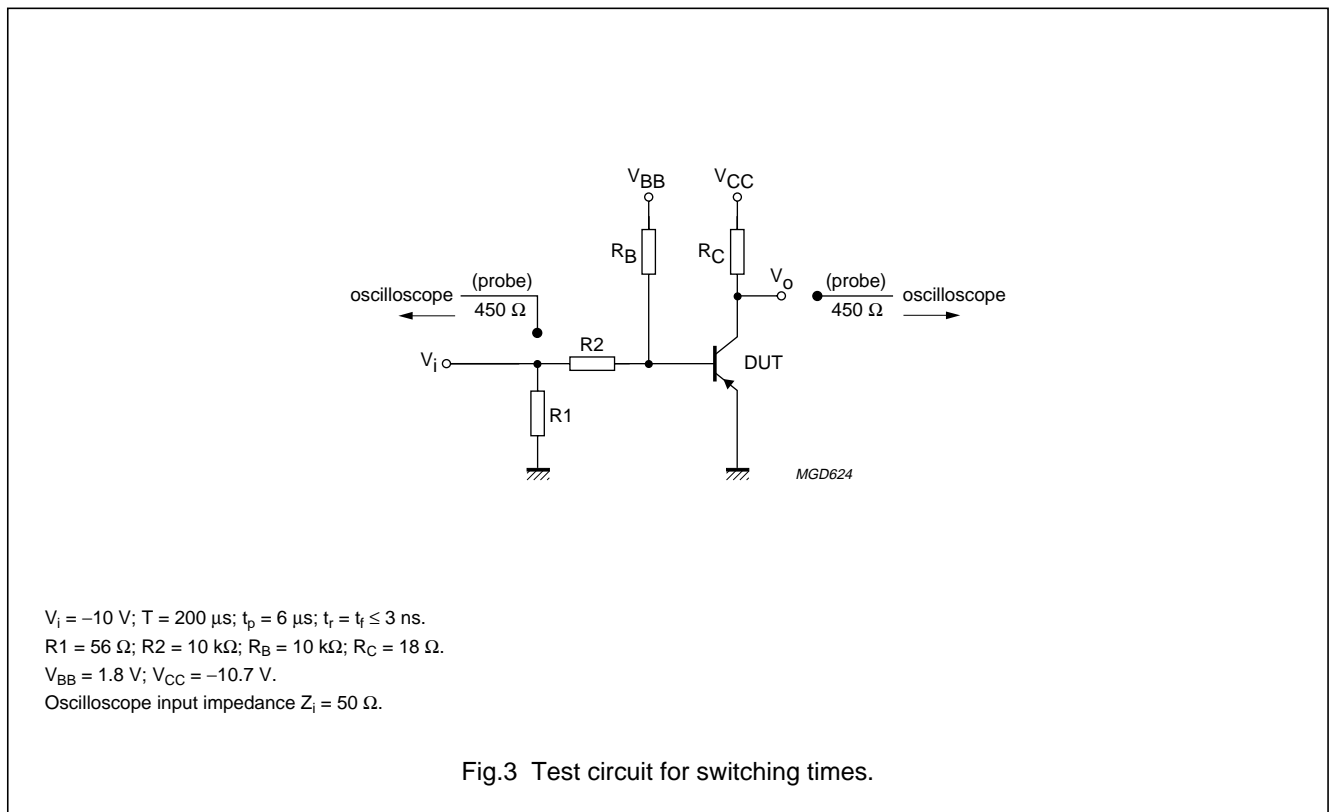
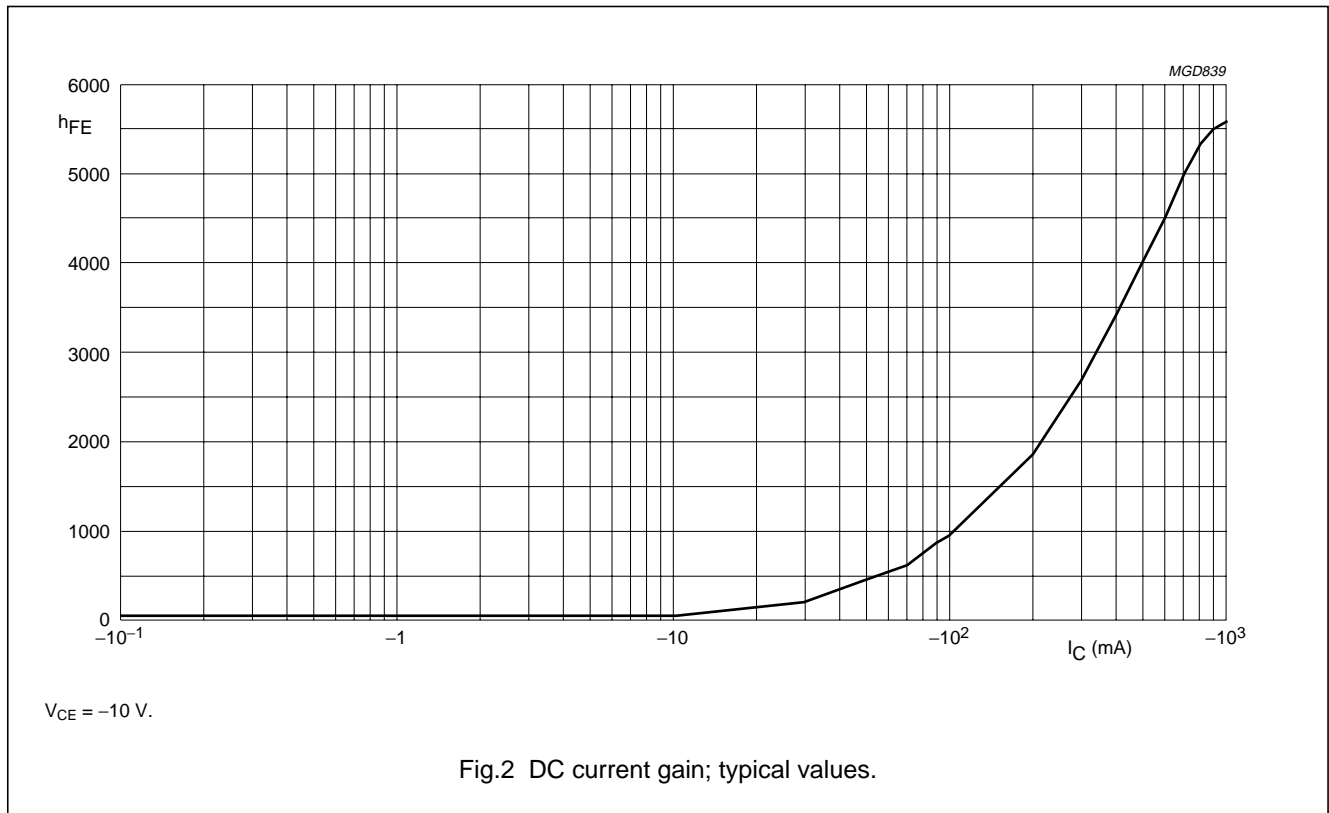
**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current BDX45	$I_E = 0; V_{CB} = -60\text{ V}$	–	–	–100	nA
		BDX47 $I_E = 0; V_{CB} = -90\text{ V}$	–	–	–100	nA
$I_{CES}$	collector cut-off current BDX45	$V_{BE} = 0; V_{CE} = -45\text{ V}$	–	–	–50	nA
		BDX47 $V_{BE} = 0; V_{CE} = -80\text{ V}$	–	–	–50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	–	–50	nA
$h_{FE}$	DC current gain	$V_{CE} = -10\text{ V}$ ; see Fig. 2 $I_C = -150\text{ mA}$ $I_C = -500\text{ mA}$	1000 2000	– –	– –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–1.3	V
		$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}; T_j = 150\text{ °C}$	–	–	–1.3	V
		$I_C = -1\text{ A}; I_B = -4\text{ mA}$	–	–	–1.6	V
		$I_C = -1\text{ A}; I_B = -4\text{ mA}; T_j = 150\text{ °C}$	–	–	–1.6	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–1.9	V
		$I_C = -1\text{ A}; I_B = -4\text{ mA}$	–	–	–2.2	V
$f_T$	transition frequency	$I_C = -500\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	–	200	–	MHz
<b>Switching times (between 10% and 90% levels); see Fig.3</b>						
$t_{on}$	turn-on time	$I_{Con} = -500\text{ mA}; I_{Bon} = -0.5\text{ mA};$ $I_{Boff} = 0.5\text{ mA}$	–	–	500	ns
$t_d$	delay time		–	–	200	ns
$t_r$	rise time		–	–	300	ns
$t_{off}$	turn-off time		–	–	700	ns
$t_s$	storage time		–	–	550	ns
$t_f$	fall time		–	–	150	ns

PNP Darlington transistors

BDX45; BDX47

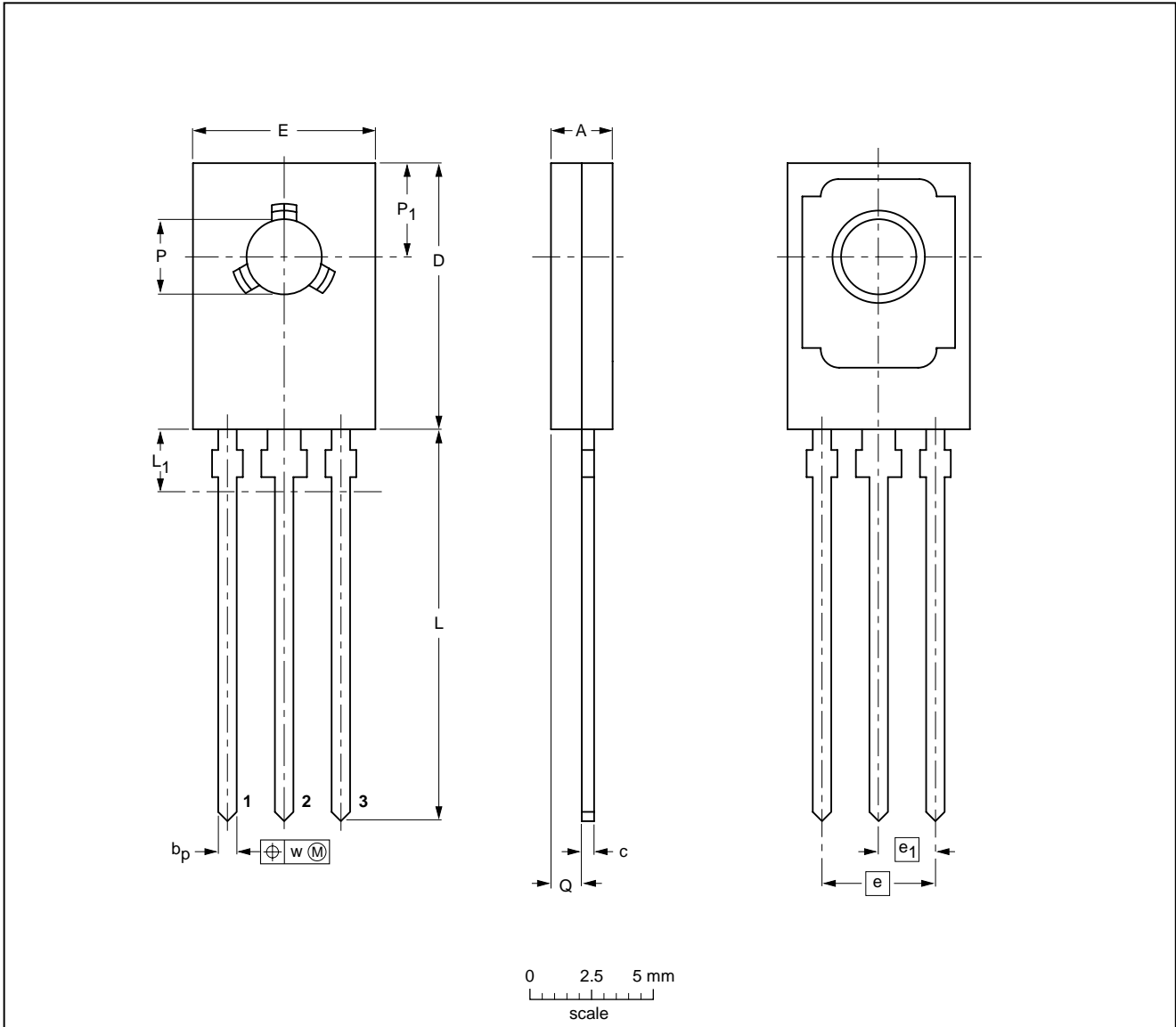


PNP Darlington transistors

BDX45; BDX47

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max	Q	P	P <sub>1</sub>	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT32		TO-126				97-03-04

## PNP Darlington transistors

## BDX45; BDX47

**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113,  
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

**Belgium:** see The Netherlands

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**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,  
Tel. +45 32 88 2636, Fax. +45 31 57 0044

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615800, Fax. +358 9 61580920

**France:** 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,  
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.  
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

**Indonesia:** see Singapore

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,  
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,  
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA,  
Tel. +48 22 612 2831, Fax. +48 22 612 2327

**Portugal:** see Spain

**Romania:** see Italy

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2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,  
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**South America:** Rua do Rocio 220, 5th floor, Suite 51,  
04552-903 São Paulo, SÃO PAULO - SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 829 1849

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 3 301 6312, Fax. +34 3 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
Tel. +46 8 632 2000, Fax. +46 8 632 2745

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**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
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**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,  
Tel. +90 212 279 2770, Fax. +90 212 282 6707

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
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**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,  
Tel. +381 11 625 344, Fax. +381 11 635 777

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